

# SILICON PNP TRANSISTOR EPITAXIAL PLANAR TYPE (PCT PROCESS)

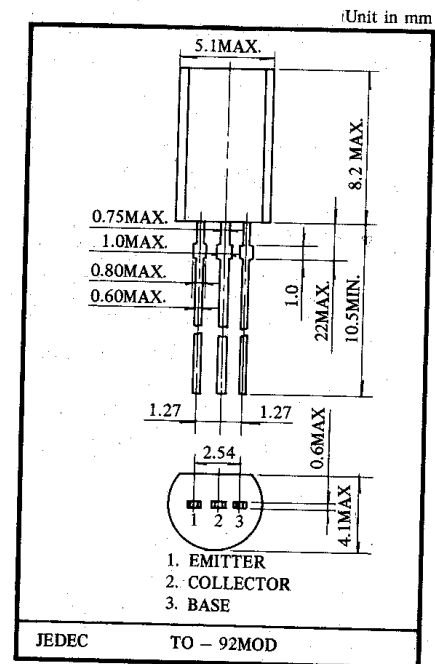
# KTA 965

## APPLICATIONS

- Power Amplifier Applications.
- Driver Stage Amplifier Applications.

## FEATURES

- Complementary to KTC 2235



## MAXIMUM RATINGS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CB0}$	-120	V	Emitter Current	$I_E$	800	mA
Collector-Emitter Voltage	$V_{CEO}$	-120	V	Collector Dissipation	$P_C$	900	mW
Emitter-Base Voltage	$V_{EBO}$	-5	V	Junction Temperature	$T_j$	150	°C
Collector Current	$I_C$	-800	mA	Storage Temperature	$T_{stg}$	-55~150	°C

## ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = -120V, I_E = 0$	-	-	-100	nA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$	-	-	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-120	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -1mA, I_C = 0$	-5	-	-	V
DC Current Gain	$h_{FE}$	$V_{CE} = -5V, I_C = -100mA$	80	-	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$	-	-	-1.0	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = -5V, I_C = -500mA$	-	-	-1.0	V
Transition Frequency	$f_T$	$V_{CE} = -5V, I_C = -100mA$	-	120	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$	-	-	40	pF

NOTE: According to  $h_{FE}$ , Classified as follows.

0	80-160	Y	120-240
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